

# Alireza Kashir

## List of Publications by Year in descending order

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Version: 2024-02-01

20  
papers

399  
citations

840776

11  
h-index

752698

20  
g-index

20  
all docs

20  
docs citations

20  
times ranked

242  
citing authors

#	ARTICLE	IF	CITATIONS
1	High polarization and wake-up free ferroelectric characteristics in ultrathin Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> devices by control of oxygen-deficient layer. <i>Nanotechnology</i> , 2022, 33, 085206.	2.6	21
2	A grease for domain walls motion in HfO <sub>2</sub> -based ferroelectrics. <i>Nanotechnology</i> , 2022, 33, 155703.	2.6	6
3	Two-step deposition of TiN capping electrodes to prevent degradation of ferroelectric properties in an in-situ crystallized TiN/Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> /TiN device. <i>Nano Express</i> , 2022, 3, 015004.	2.4	1
4	Hafnium Oxide (HfO <sub>2</sub> ) – A Multifunctional Oxide: A Review on the Prospect and Challenges of Hafnium Oxide in Resistive Switching and Ferroelectric Memories. <i>Small</i> , 2022, 18, e2107575.	10.0	78
5	Improvement of endurance and switching speed in Hf <sub>1-x</sub> Zr <sub>x</sub> O <sub>2</sub> thin films using a nanolaminate structure. <i>Nanotechnology</i> , 2022, 33, 395205.	2.6	2
6	Defect Engineering to Achieve Wake-up Free HfO <sub>2</sub> -Based Ferroelectrics. <i>Advanced Engineering Materials</i> , 2021, 23, .	3.5	53
7	Towards an ideal high- $\epsilon^*$ HfO <sub>2</sub> -ZrO <sub>2</sub> -based dielectric. <i>Nanoscale</i> , 2021, 13, 13631-13640.	5.6	18
8	Large Remnant Polarization in a Wake-Up Free Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> Ferroelectric Film through Bulk and Interface Engineering. <i>ACS Applied Electronic Materials</i> , 2021, 3, 629-638.	4.3	79
9	Ferroelectric and Dielectric Properties of Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> Thin Film Near Morphotropic Phase Boundary. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000819.	1.8	18
10	Effects of high pressure oxygen annealing on Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> ferroelectric device. <i>Nanotechnology</i> , 2021, 32, 315712.	2.6	11
11	A CMOS-compatible morphotropic phase boundary. <i>Nanotechnology</i> , 2021, 32, 445706.	2.6	12
12	A new approach to achieving strong ferroelectric properties in TiN/Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> /TiN devices. <i>Nanotechnology</i> , 2021, 32, 055703.	2.6	21
13	Hf <sub>1-x</sub> Zr <sub>x</sub> O <sub>2</sub> /ZrO <sub>2</sub> Nanolaminate Thin Films as a High- $\epsilon^*$ Dielectric. <i>ACS Applied Electronic Materials</i> , 2021, 3, 5632-5640.	4.3	12
14	Effect of dead layers on the ferroelectric property of ultrathin HfZrOx film. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	37
15	Strain effect on magnetic-exchange-induced phonon splitting in NiO films. <i>Journal of Physics Condensed Matter</i> , 2020, 32, 405607.	1.8	2
16	Spin-phonon interaction increased by compressive strain in antiferromagnetic MnO thin films. <i>Journal of Physics Condensed Matter</i> , 2020, 32, 175402.	1.8	1
17	A thin film perspective on quantum functional oxides. <i>Current Applied Physics</i> , 2019, 19, 207-214.	2.4	6
18	Strain-Induced Increase of Dielectric Constant in EuO Thin Film. <i>Materials Research Express</i> , 2019, 6, 106321.	1.6	5

#	ARTICLE	IF	CITATIONS
19	Dielectric Properties of Strained Nickel Oxide Thin Films. Journal of the Korean Physical Society, 2019, 74, 984-988.	0.7	11
20	Pulsed Laser Deposition of Rocksalt Magnetic Binary Oxides. Thin Solid Films, 2019, 692, 137606.	1.8	5